

Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

[Vishay/Siliconix](#)

[SI1404BDH-T1-E3](#)

For any questions, you can email us directly:

sales@integrated-circuit.com



Si1404BDH
Vishay Siliconix

N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY

V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
30	0.238 at V _{GS} = 4.5 V	1.9	1.1 nC
	0.380 at V _{GS} = 2.5 V	1.51	

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

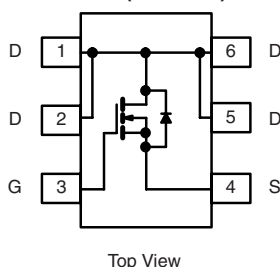


RoHS
COMPLIANT
HALOGEN
FREE
Available

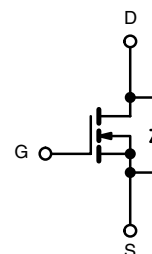
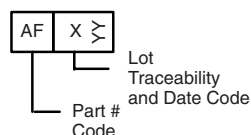
APPLICATIONS

- Load Switch for Portable Device

SC-70 (6-LEADS)



Marking Code



Ordering Information: Si1404BDH-T1-E3 (Lead (Pb)-free)
Si1404BDH-T1-GE3 (Lead (Pb)-free and Halogen-free)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	± 12	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	A
		T _C = 70 °C	
		T _A = 25 °C	
		T _A = 70 °C	
Pulsed Drain Current	I _{DM}	4	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	W
Maximum Power Dissipation	P _D	T _C = 25 °C	
		T _C = 70 °C	
		T _A = 25 °C	
		T _A = 70 °C	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^d	R _{thJA}	70	85	°C/W
Maximum Junction-to-Foot (Drain)	R _{thJF}	44	55	

Notes:

- Based on T_C = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- Maximum under steady state conditions is 100 °C/W.

Si1404BDH

Vishay Siliconix



SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	30			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		27.3		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			3		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.6		1.3	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 12 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			1	μA
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 4.5 V	4			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 1.9		0.190	0.238	Ω
		V _{GS} = 2.5 V, I _D = 1.51		0.30	0.380	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 1.9		2		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		100		pF
Output Capacitance	C _{oss}			30		
Reverse Transfer Capacitance	C _{rss}			20		
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 1.9 A		1.8	2.7	nC
Gate-Source Charge	Q _{gs}	V _{DS} = 15 V, V _{GS} = 2.5 V, I _D = 1.9 A		1.1	1.7	
Gate-Drain Charge	Q _{gd}			0.4		
Gate Resistance	R _g			0.6		
Turn-On Delay Time	t _{d(on)}	f = 1 MHz V _{DD} = 15 V, R _L = 9.87 Ω I _D ≅ 1.52 A, V _{GEN} = 4.5 V, R _g = 1 Ω		1.5	2.3	Ω
Rise Time	t _r			10	15	ns
Turn-Off Delay Time	t _{d(off)}			30	45	
Fall Time	t _f			5	7.5	
				10	15	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			0.31	A
Pulse Diode Forward Current ^a	I _{SM}				4	
Body Diode Voltage	V _{SD}	I _S = 1.1 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 1.1 A, dI/dt = 100 A/μs, T _J = 25 °C		55	85	ns
Body Diode Reverse Recovery Charge	Q _{rr}			105	160	nC
Reverse Recovery Fall Time	t _a			34		ns
Reverse Recovery Rise Time	t _b			16		

Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

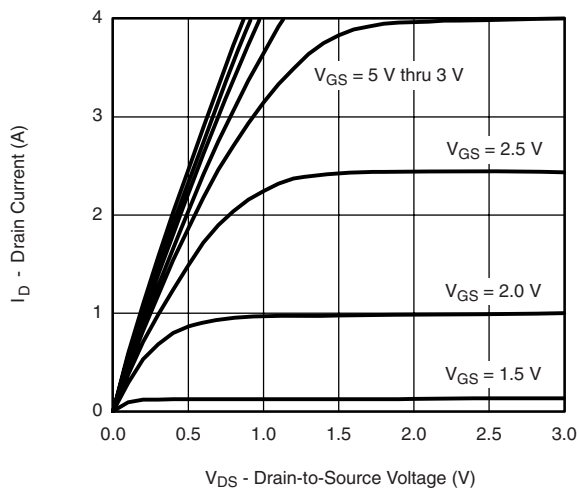
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



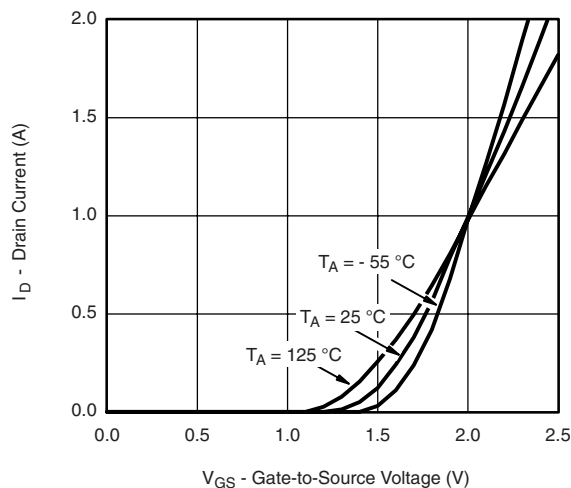
Si1404BDH

Vishay Siliconix

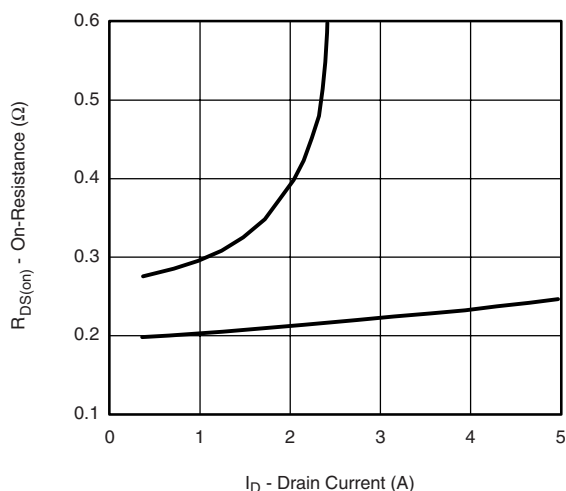
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



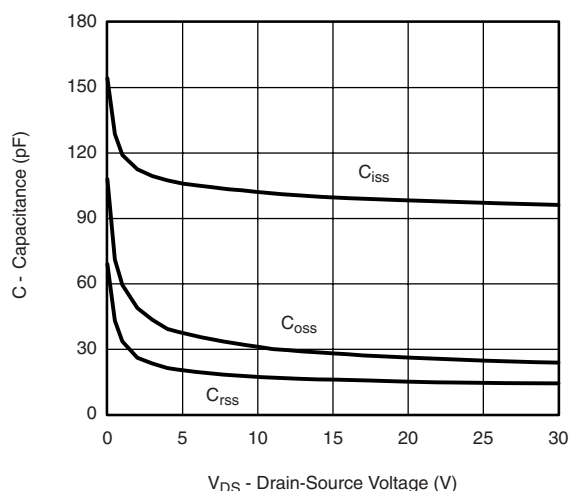
Output Characteristics



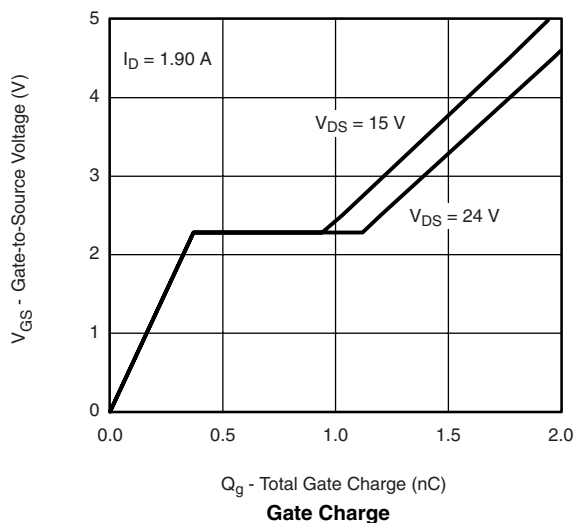
Transfer Characteristics Curves vs. Temperature



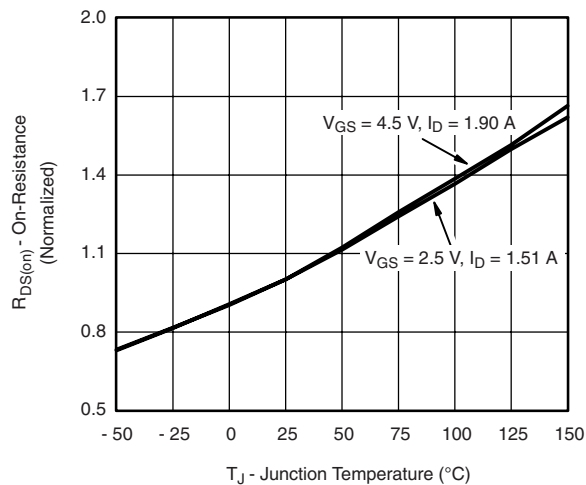
On-Resistance vs. Drain Current



Capacitance



Gate Charge



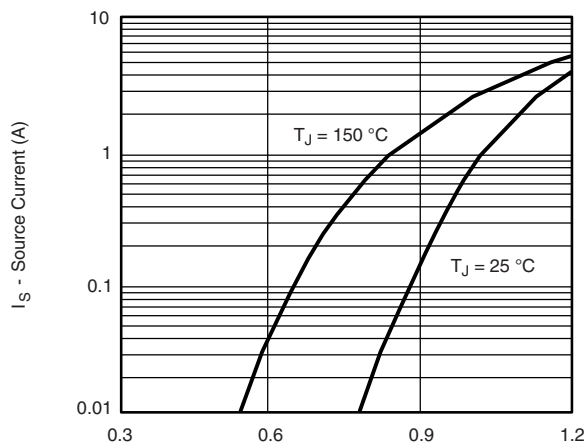
On-Resistance vs. Junction Temperature

Si1404BDH

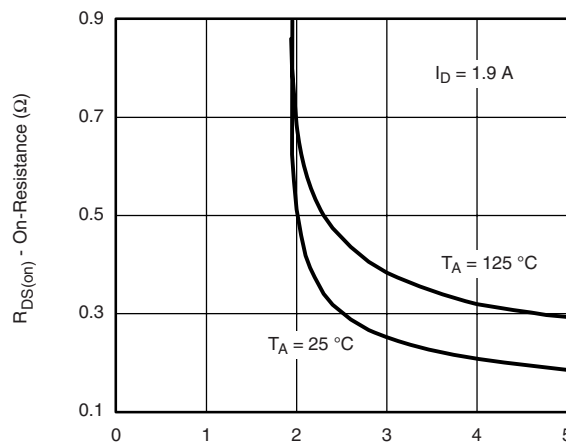
Vishay Siliconix



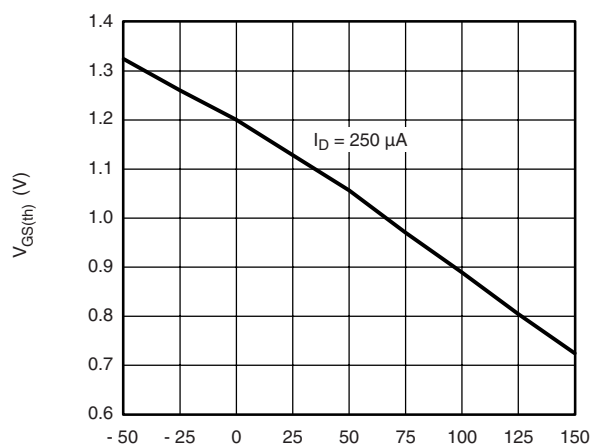
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



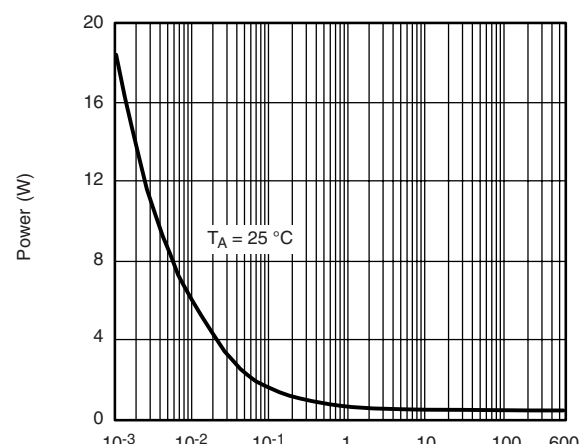
V_{SD} - Source-to-Drain Voltage (V)
Forward Diode Voltage vs. Temp



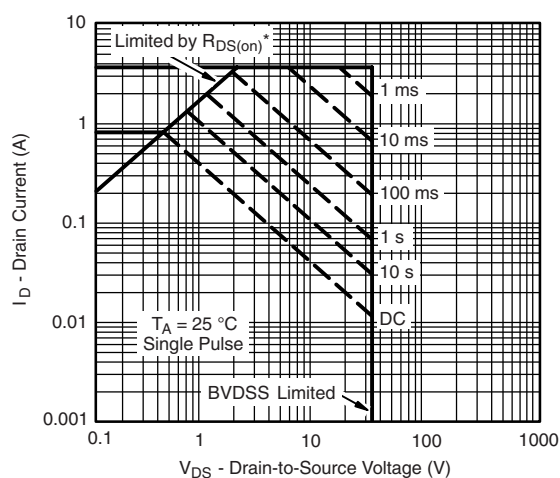
V_{GS} - Gate-to-Source Voltage (V)
On-Resistance vs. Gate-to-Source Voltage



T_J - Temperature ($^{\circ}\text{C}$)
Threshold Voltage



Single Pulse Power, Junction-to-Ambient



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

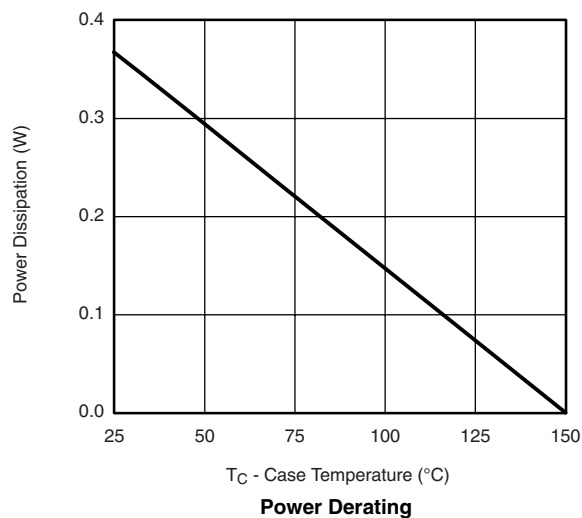
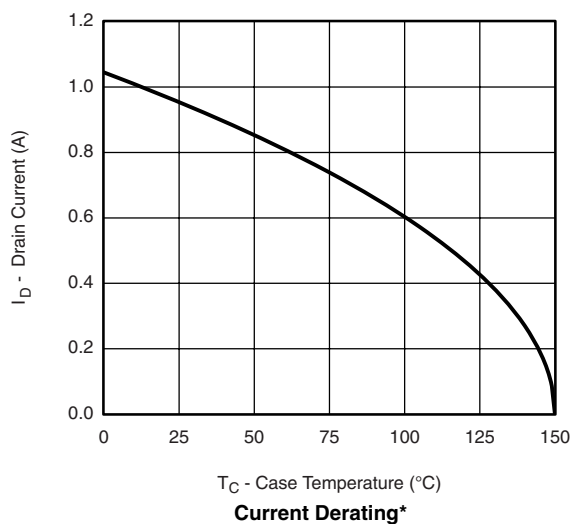
Safe Operating Area



Si1404BDH

Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



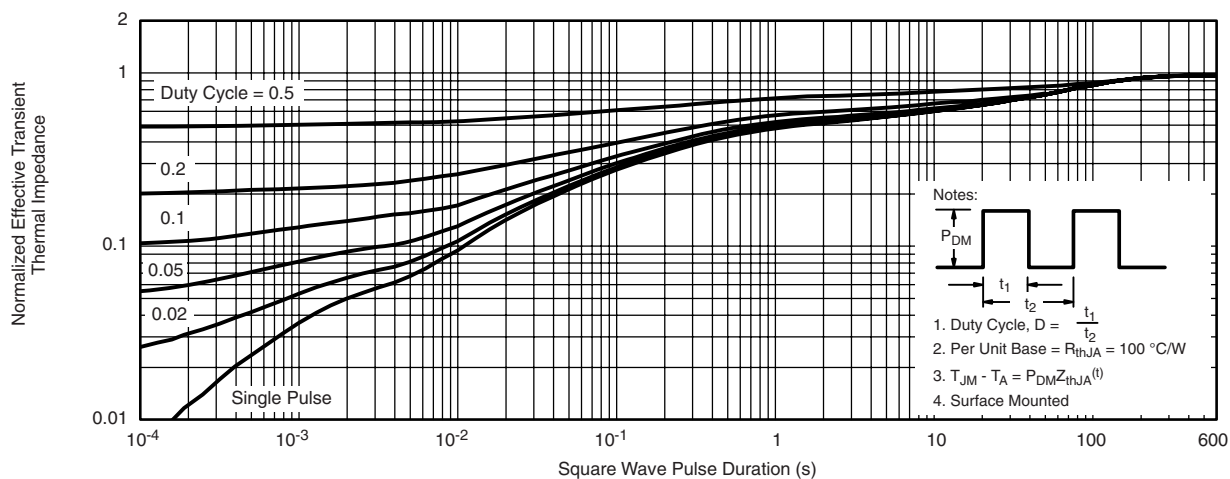
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

Si1404BDH

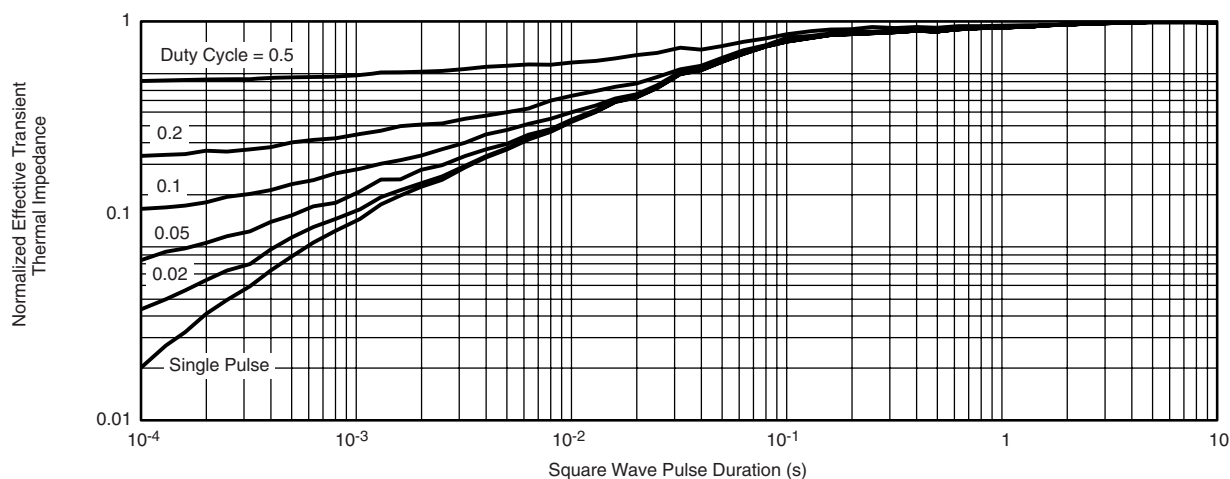
Vishay Siliconix



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg773487.



Legal Disclaimer Notice

Vishay

Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.